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APPLICATION NO.	FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/504,782	0	2/15/2000	Masahiro Kume	0819-337	8307
22204	7590	03/31/2003			
NIXON PEA	•		EXAMINER		
8180 GREEN SUITE 800	SBORO I	DRIVE	FLORES RUIZ, DELMA R		
MCLEAN, V	A 22102			ART UNIT	PAPER NUMBER
				2828	
				DATE MAILED: 03/31/2003	

Please find below and/or attached an Office communication concerning this application or proceeding.

· · ·	Application.	Applicant(s)	
	09/504,782	KUME ET AL.	
Office Action Summary	Examiner	Art Unit	
	Delma R. Flores Ruiz	2828	•
The MAILING DATE of this communication Period for Reply	appears on the cover sheet wi	th the correspondence address	•
A SHORTENED STATUTORY: PERIOD FOR RE THE MAILING DATE OF THIS COMMUNICATIO Extensions of time may be available under the provisions of 37 CFr after SIX (6) MONTHS from the mailing date of this communication If the period for reply specified above is less than thirty (30) days, a If NO period for reply is specified above, the maximum statutory pe Failure to reply within the set or extended period for reply will, by st Any reply received by the Office later than three months after the mearned patent term adjustment. See 37 CFR 1.704(b). Status	DN. R 1.136(a). In no event, however, may a relation. In a reply within the statutory minimum of thirt riod will apply and will expire SIX (6) MON tatute, cause the application to become AB	pply be timely filed y (30) days will be considered timely. THS from the mailing date of this communication ANDONED (35 U.S.C. § 133).	on.
1) Responsive to communication(s) filed on	<u> 26 December 2002</u> .		
2a)⊠ This action is FINAL . 2b)□	This action is non-final.		
3) Since this application is in condition for all closed in accordance with the practice uno Disposition of Claims			is
4) Claim(s) 1-6 is/are pending in the applicati	ion.		
4a) Of the above claim(s) 7-35 is/are withdr	rawn from consideration.	θ α α	
5) Claim(s) is/are allowed.		Paul Do	
6)⊠ Claim(s) <u>1-6</u> is/are rejected.		, Paul ip	
7) Claim(s) is/are objected to.		SUPERVISORY PATENT EXAMI	NER
8) Claim(s) are subject to restriction an	nd/or election requirement.	TECHNOLOGY CENTER 280	0
Application Papers			
9)☐ The specification is objected to by the Exam	niner.		
10) The drawing(s) filed on is/are: a) a	ccepted or b) objected to by t	ne Examiner.	
Applicant may not request that any objection t	<u> </u>	• •	
11) The proposed drawing correction filed on		sapproved by the Examiner.	
If approved, corrected drawings are required in	, ,		
12) ☐ The oath or declaration is objected to by the	Examiner.		
Priority under 35 U.S.C. §§ 119 and 120			
13) Acknowledgment is made of a claim for for	eign priority under 35 U.S.C. §	119(a)-(d) or (f).	
a) ☐ All b) ☐ Some * c) ☐ None of:			
 Certified copies of the priority docum 	ents have been received.		
2. Certified copies of the priority docum	ents have been received in A	oplication No	
 3. Copies of the certified copies of the paper application from the International * See the attached detailed Office action for a 	Bureau (PCT Rule 17.2(a)).	•	
14) Acknowledgment is made of a claim for dom	•		tion)
a) The translation of the foreign language			non).
15) Acknowledgment is made of a claim for dom			
Attachment(s)			
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449) Paper Note 	5) Notice of I	Summary (PTO-413) Paper No(s) nformal Patent Application (PTO-152)	
S. Patent and Trademark Office PTO-326 (Rev. 04-01) Office	e Action Summary	Part of Paper No.	11

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DETAILED ACTION

Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claims 1 – 6 are recites the limitation " $x \ge y$ " in claim 1, line 11 and claim 4, line

12. There is insufficient antecedent basis for this limitation in the claim.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

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Claims 1 – 6 are rejected under 35 U.S.C. 102(b) as being anticipated by Furukawa et al (5,981,977).

Regarding claims 1 − *3,* Furukawa discloses a semiconductor laser device comprising; a first cladding (see Fig. 2C Character 24) layer, which is mace of a nitride semiconductor of a first conductivity type and is formed over a substrate (see Fig. 2C Character 12); an active layer (see Fig. 2C Character 26), which is mode of, which is made $\ln_x \operatorname{Ga}_{1-x} \operatorname{N}$ layer and is formed over the first cladding layer; and a second cladding (see Fig. 2C Character 28) layer, which is made of still another nitride semiconductor of a second conductivity type and is formed over the active layer, wherein $\ln_x \operatorname{Ga}_{1-x} \operatorname{N}$ layer of the first conductivity type is formed between the substrate and the first cladding layer and $x \ge y$ in the composition on \ln (see Figs. 2A-D, Abstract, Column 1, lines 27 − 59, Column 2, lines 1 − 11, 29 − 44, 53 − 63, Column 4, lines 20 − 64). The spontaneous emission-absorbing layer contains indium and is formed in contact with the first cladding layer and substrate (see Fig. 2A-D, Column 8, lines 6 − 16, Column 10, lines 7 − 23).

Regarding claims 4 – 6, Furukawa discloses a semiconductor laser device comprising; a first cladding (see Fig. 2C Character 24) layer, which is mace of a nitride semiconductor of a first conductivity type and is formed over a substrate (see Fig. 2C Character 12); an active layer (see Fig. 2C Character 26) layer, which is mode of In_x Ga_{1-x}N and is formed over the first cladding layer; and a second cladding layer (see Fig.

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2C Character 28), which is made of still another nitride semiconductor of a second conductivity type and is formed over the active layer, an electrode (see Fig. 1A Character 50 and 52) formed over the second cladding layer; wherein In_x $Ga_{1-x}N$ of the second conductivity type and is formed between the second cladding layer and $x \succeq y$ in the composition on In and electrode (see Figs. 2A-D, Abstract, Column 1, lines 27 - 59, Column 2, lines 1 - 11, 29 - 44, 53 - 63, Column 4, lines 20 - 64). The spontaneous emission-absorbing layer contains indium and is formed in contact with the second cladding layer and electrode (see Fig. 2A-D, Column 8, lines 6 - 16, Column 10, lines 7 - 23).

Response to Arguments

Applicant's arguments with respect to claims 1 – 6 have been considered but are moot in view of the new ground(s) of rejection. Applicants amendments raised new issues that made necessary the new art to be applied and therefore, the arguments presented against Furukawa are said to be moot due to the new grounds of rejection. Also, the arguments presented have been fully addressed in the above presented rejection.

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Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Delma R. Flores Ruiz whose telephone number is (703) 308-6238. The examiner can normally be reached on M - F.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Paul Ip can be reached on (703) 308-3098. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7724 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 306-3431.

Examiner
Art Unit 2828

DRFR/PI March 20, 2003 Paul Ip Supervisor Patent Examiner Art Unit 2828